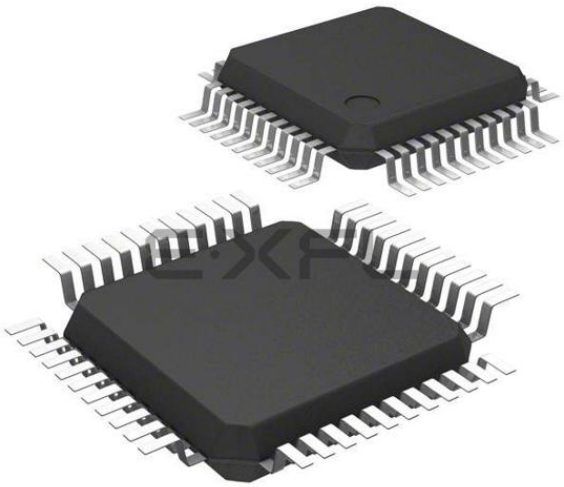
Renesas Electronics America Inc - R5F104FGAFP#50 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	31
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104fgafp-50

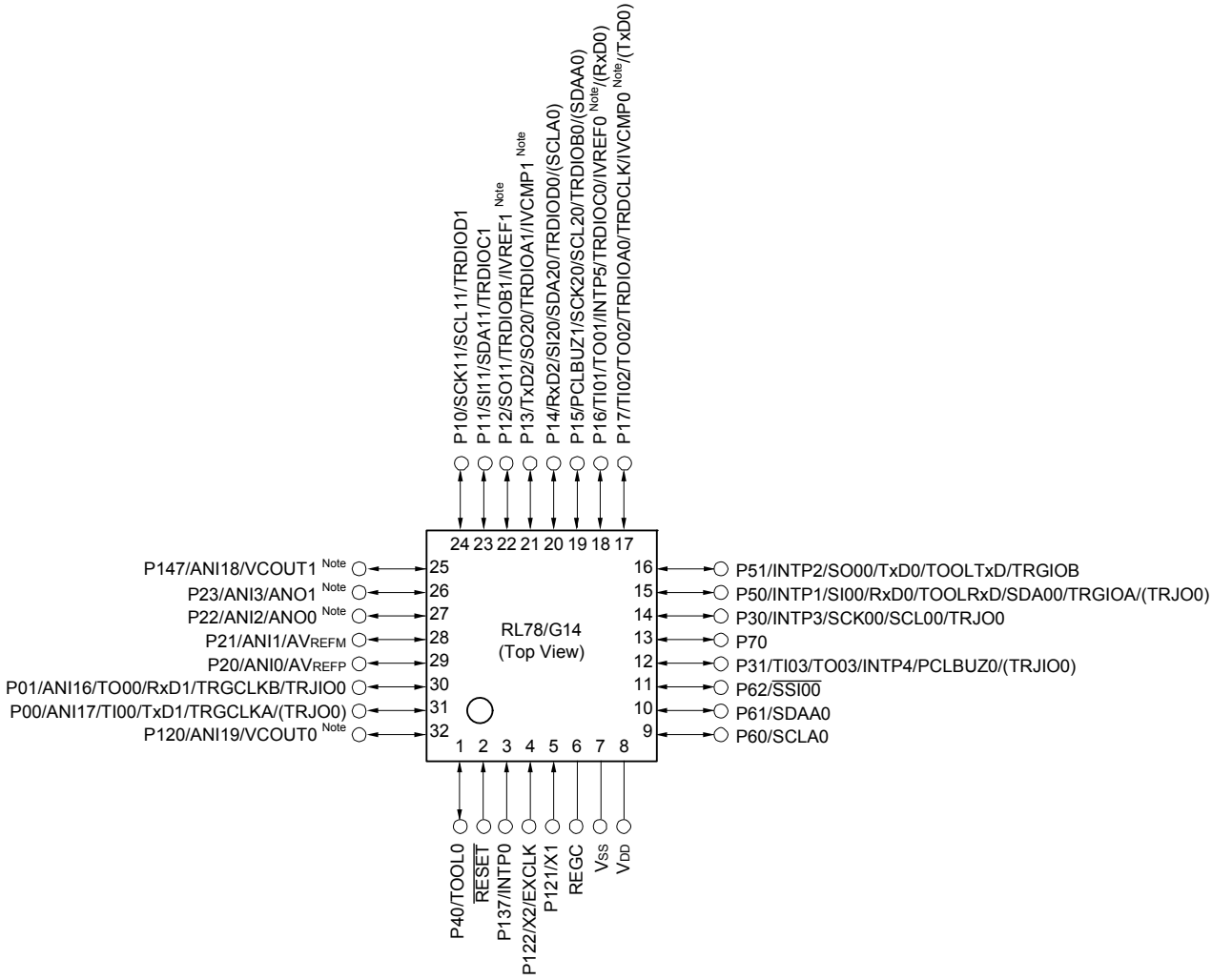
(5/5)

Pin count	Package	Fields of Application Note	Ordering Part Number
80 pins	80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)	A	R5F104MFAFB#V0, R5F104MGAFB#V0, R5F104MHAFB#V0, R5F104MJAFB#V0 R5F104MFAFB#X0, R5F104MGAFB#X0, R5F104MHAFB#X0, R5F104MJAFB#X0 R5F104MKAFB#30, R5F104MLAFB#30 R5F104MKAFB#50, R5F104MLAFB#50
		D	R5F104MFDFB#V0, R5F104MGDFB#V0, R5F104MHDFB#V0, R5F104MJDFB#V0 R5F104MFDFB#X0, R5F104MGDFB#X0, R5F104MHDFB#X0, R5F104MJDFB#X0
		G	R5F104MFGFB#V0, R5F104MGGFB#V0, R5F104MHGFB#V0, R5F104MJGFB#V0 R5F104MFGFB#X0, R5F104MGGFB#X0, R5F104MHGFB#X0, R5F104MJGFB#X0 R5F104MKGFB#30, R5F104MLGFB#30 R5F104MKGFB#X0, R5F104MLGFB#50
	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	A	R5F104MFAFA#V0, R5F104MGAFA#V0, R5F104MHAFA#V0, R5F104MJAFA#V0 R5F104MFAFA#X0, R5F104MGAFA#X0, R5F104MHAFA#X0, R5F104MJAFA#X0 R5F104MKAFA#30, R5F104MLAFA#30 R5F104MKAFA#50, R5F104MLAFA#50
		D	R5F104MFDFA#V0, R5F104MGDFA#V0, R5F104MHDFA#V0, R5F104MJDFA#V0 R5F104MFDFA#X0, R5F104MGDFA#X0, R5F104MHDFA#X0, R5F104MJDFA#X0
		G	R5F104MFGFA#V0, R5F104MGGFA#V0, R5F104MHGFA#V0, R5F104MJGFA#V0 R5F104MFGFA#X0, R5F104MGGFA#X0, R5F104MHGFA#X0, R5F104MJGFA#X0 R5F104MKGFA#30, R5F104MLGFA#30 R5F104MKGFA#50, R5F104MLGFA#50
100 pins	100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)	A	R5F104PFAFB#V0, R5F104PGAFB#V0, R5F104PHAFB#V0, R5F104PJAFB#V0 R5F104PFAFB#X0, R5F104PGAFB#X0, R5F104PHAFB#X0, R5F104PJAFB#X0 R5F104PKAFB#30, R5F104PLAFB#30 R5F104PKAFB#50, R5F104PLAFB#50
		D	R5F104PFDFB#V0, R5F104PGDFB#V0, R5F104PHDFB#V0, R5F104PJDFB#V0 R5F104PFDFB#X0, R5F104PGDFB#X0, R5F104PHDFB#X0, R5F104PJDFB#X0
		G	R5F104PFGFB#V0, R5F104PGGFB#V0, R5F104PHGFB#V0, R5F104PJGFB#V0 R5F104PFGFB#X0, R5F104PGGFB#X0, R5F104PHGFB#X0, R5F104PJGFB#X0 R5F104PKGFB#30, R5F104PLGFB#30 R5F104PKGFB#50, R5F104PLGFB#50
	100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)	A	R5F104PFAFA#V0, R5F104PGAFA#V0, R5F104PHAFA#V0, R5F104PJAFA#V0 R5F104PFAFA#X0, R5F104PGAFA#X0, R5F104PHAFA#X0, R5F104PJAFA#X0 R5F104PKAFA#30, R5F104PLAFA#30 R5F104PKAFA#50, R5F104PLAFA#50
		D	R5F104PFDFA#V0, R5F104PGDFA#V0, R5F104PHDFA#V0, R5F104PJDFA#V0 R5F104PFDFA#X0, R5F104PGDFA#X0, R5F104PHDFA#X0, R5F104PJDFA#X0
		G	R5F104PFGFA#V0, R5F104PGGFA#V0, R5F104PHGFA#V0, R5F104PJGFA#V0 R5F104PFGFA#X0, R5F104PGGFA#X0, R5F104PHGFA#X0, R5F104PJGFA#X0 R5F104PKGFA#30, R5F104PLGFA#30 R5F104PKGFA#50, R5F104PLGFA#50

Note For the fields of application, refer to **Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14**.

Caution **The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.**

• 32-pin plastic LQFP (7 × 7 mm, 0.8 mm pitch)



Note Mounted on the 96 KB or more code flash memory products.

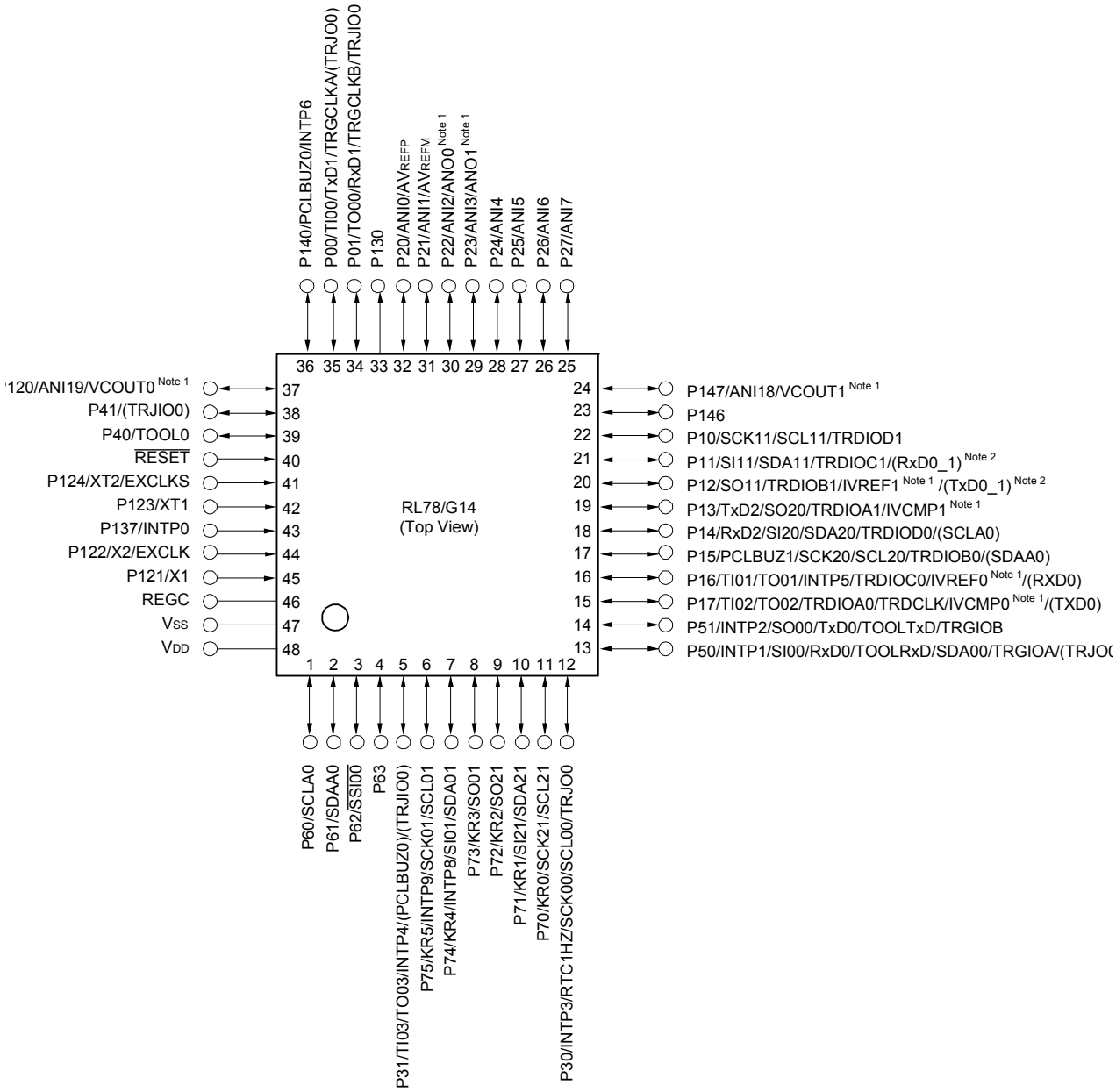
Caution **Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μF).**

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

1.3.6 48-pin products

• 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)



Note 1. Mounted on the 96 KB or more code flash memory products.

Note 2. Mounted on the 384 KB or more code flash memory products.

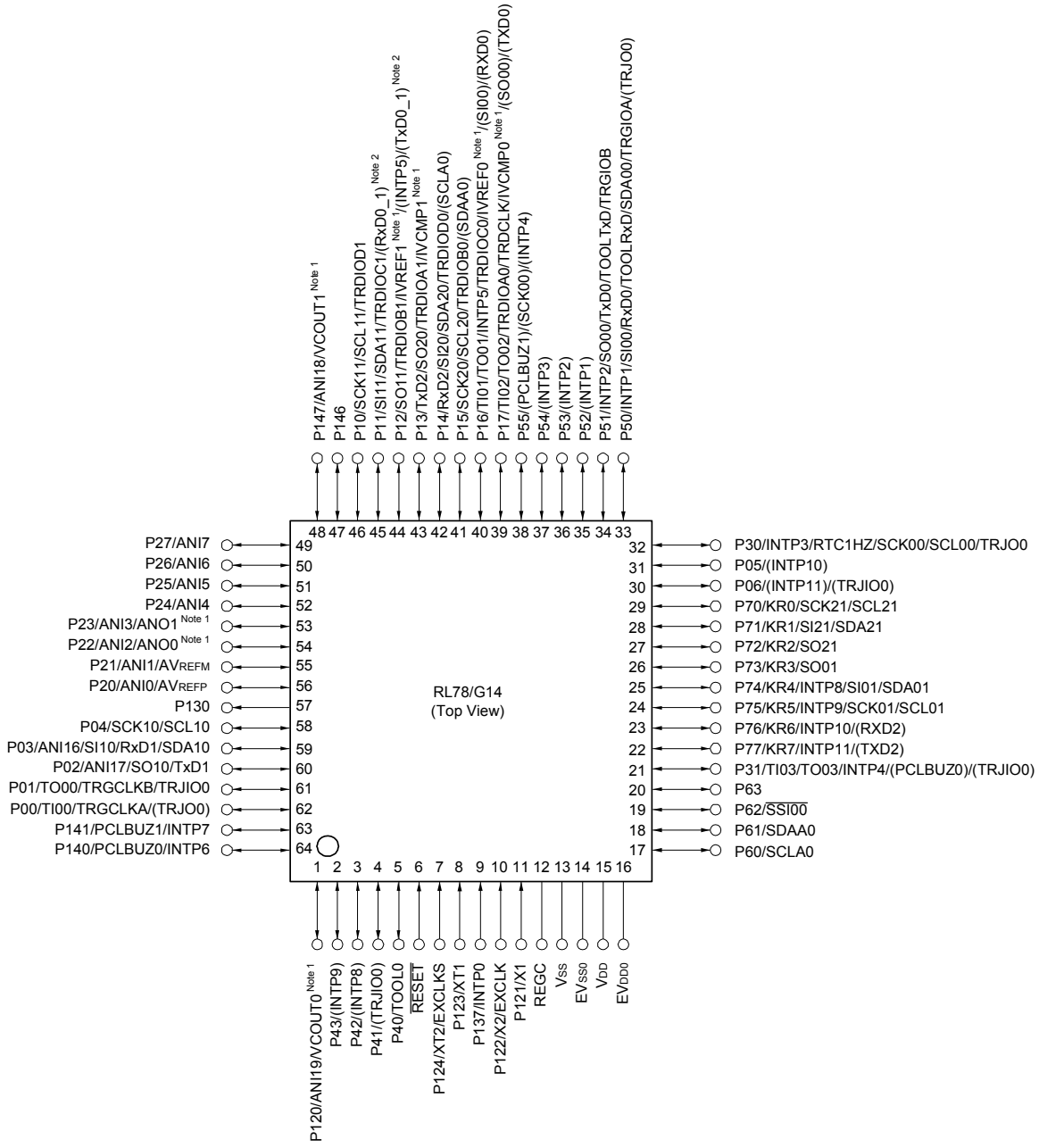
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μF).

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

1.3.8 64-pin products

- 64-pin plastic LQFP (14 × 14 mm, 0.8 mm pitch)
- 64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)
- 64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)



Note 1. Mounted on the 96 KB or more code flash memory products.

Note 2. Mounted on the 384 KB or more code flash memory products.

Caution 1. Make EV_{SS0} pin the same potential as V_{SS} pin.

Caution 2. Make V_{DD} pin the potential that is higher than EV_{DD0} pin.

Caution 3. Connect the REGC pin to V_{SS} pin via a capacitor (0.47 to 1 μF).

Remark 1. For pin identification, see **1.4 Pin Identification**.

Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the V_{SS} and EV_{SS0} pins to separate ground lines.

Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

(2/2)

Item		30-pin R5F104Ax (x = F, G)	32-pin R5F104Bx (x = F, G)	36-pin R5F104Cx (x = F, G)	40-pin R5F104Ex (x = F to H)
Clock output/buzzer output		2	2	2	2
		[30-pin, 32-pin, 36-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) [40-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)			
8/10-bit resolution A/D converter		8 channels	8 channels	8 channels	9 channels
D/A converter		1 channel	2 channels		
Comparator		2 channels			
Serial interface		[30-pin, 32-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel [36-pin, 40-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 2 channels/UART: 1 channel/simplified I^2C: 2 channels			
	I^2C bus	1 channel	1 channel	1 channel	1 channel
Data transfer controller (DTC)		30 sources			31 sources
Event link controller (ELC)		Event input: 21 Event trigger output: 8	Event input: 21, Event trigger output: 9		Event input: 22 Event trigger output: 9
Vectored interrupt sources	Internal	24	24	24	24
	External	6	6	6	7
Key interrupt		—	—	—	4
Reset		• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution Note • Internal reset by RAM parity error • Internal reset by illegal-memory access			
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V (T_A = –40 to +85°C) 1.51 ±0.06 V (T_A = –40 to +105°C) • Power-down-reset: 1.50 ±0.04 V (T_A = –40 to +85°C) 1.50 ±0.06 V (T_A = –40 to +105°C)			
Voltage detector		1.63 V to 4.06 V (14 stages)			
On-chip debug function		Provided			
Power supply voltage		V_{DD} = 1.6 to 5.5 V (T_A = –40 to +85°C) V_{DD} = 2.4 to 5.5 V (T_A = –40 to +105°C)			
Operating ambient temperature		T_A = –40 to +85°C (A: Consumer applications, D: Industrial applications), T_A = -40 to +105°C (G: Industrial applications)			

Note The illegal instruction is generated when instruction code FFH is executed.
Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F104xD (x = A to C, E to G, J, L): Start address FE900H
R5F104xE (x = A to C, E to G, J, L): Start address FE900H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F104xL (x = G, L, M, P): Start address F3F00H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = 0 V)(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.80	3.09	mA
					V_{DD} = 3.0 V		0.80	3.09	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.49	2.40	
					V_{DD} = 3.0 V		0.49	2.40	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.62	2.40	
					V_{DD} = 3.0 V		0.62	2.40	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.4	1.83	
					V_{DD} = 3.0 V		0.4	1.83	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		0.37	1.38	
					V_{DD} = 3.0 V		0.37	1.38	
			LS (low-speed main) mode Note 7	f_{HOCO} = 8 MHz, f_{IH} = 8 MHz Note 4	V_{DD} = 3.0 V		260	710	μA
					V_{DD} = 2.0 V		260	710	
			LV (low-voltage main) mode Note 7	f_{HOCO} = 4 MHz, f_{IH} = 4 MHz Note 4	V_{DD} = 3.0 V		420	700	μA
					V_{DD} = 2.0 V		420	700	
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.28	1.55	mA
					Resonator connection		0.40	1.74	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.28	1.55	
					Resonator connection		0.40	1.74	
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.19	0.86	
					Resonator connection		0.25	0.93	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.19	0.86	
					Resonator connection		0.25	0.93	
			LS (low-speed main) mode Note 7	f_{MX} = 8 MHz Note 3, V_{DD} = 3.0 V	Square wave input		95	550	μA
					Resonator connection		140	590	
				f_{MX} = 8 MHz Note 3, V_{DD} = 2.0 V	Square wave input		95	550	
					Resonator connection		140	590	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5, T_A = -40°C	Square wave input		0.25	0.57	μA
					Resonator connection		0.44	0.76	
				f_{SUB} = 32.768 kHz Note 5, T_A = +25°C	Square wave input		0.30	0.57	
					Resonator connection		0.49	0.76	
				f_{SUB} = 32.768 kHz Note 5, T_A = +50°C	Square wave input		0.36	1.17	
					Resonator connection		0.59	1.36	
				f_{SUB} = 32.768 kHz Note 5, T_A = +70°C	Square wave input		0.49	1.97	
					Resonator connection		0.72	2.16	
				f_{SUB} = 32.768 kHz Note 5, T_A = +85°C	Square wave input		0.97	3.37	
					Resonator connection		1.16	3.56	
	I_{DD3} Note 6	STOP mode Note 8	T_A = -40°C				0.18	0.51	μA
			T_A = +25°C				0.24	0.51	
			T_A = +50°C				0.29	1.10	
			T_A = +70°C				0.41	1.90	
			T_A = +85°C				0.90	3.30	

(**Notes** and **Remarks** are listed on the next page.)

Note 1. Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. During HALT instruction execution by flash memory.

Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 4. When high-speed system clock and subsystem clock are stopped.

Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.

Note 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

Note 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

Note 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (64 MHz max.)

Remark 3. f_{IH}: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	$t_{SU:DAT}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 135 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 135 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		1/f_{MCK} + 190 Note 3		ns
Data hold time (transmission)	$t_{HD:DAT}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	0	305	0	305	0	305	ns
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	0	355	0	355	0	355	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	0	405	0	405	0	405	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

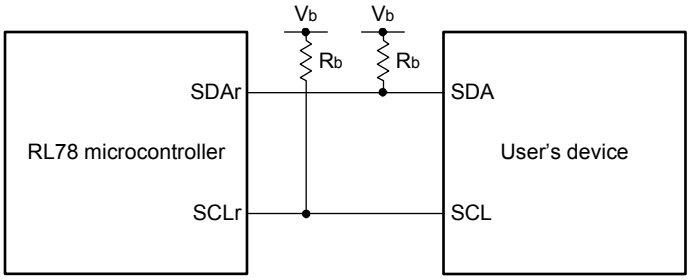
Note 2. Use it with EV_{DD0} ≥ V_b.

Note 3. Set the f_{MCK} value to keep the hold time of SCLr = “L” and SCLr = “H”.

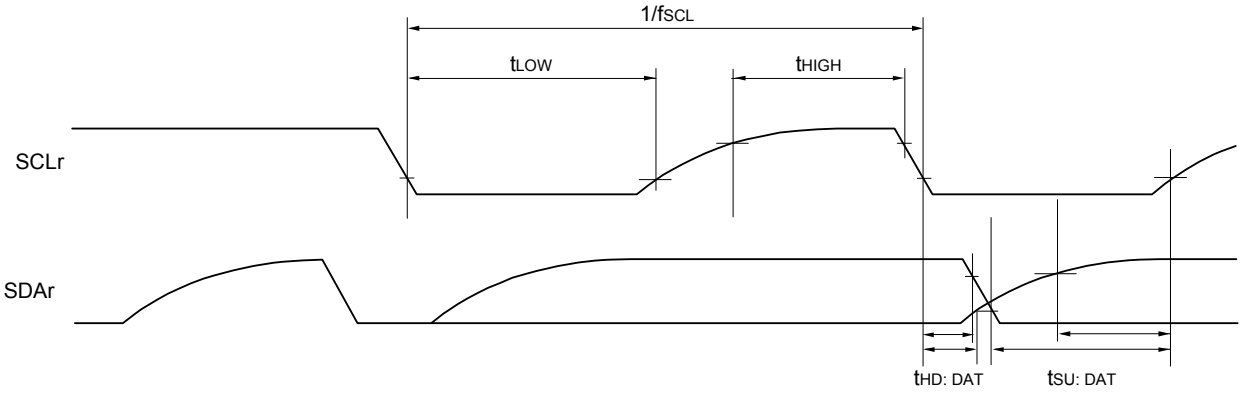
Caution Select the TTL input buffer and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 01, 10, 11, 20, 30, 31), g: PIM, POM number (g = 0, 1, 3 to 5, 14)

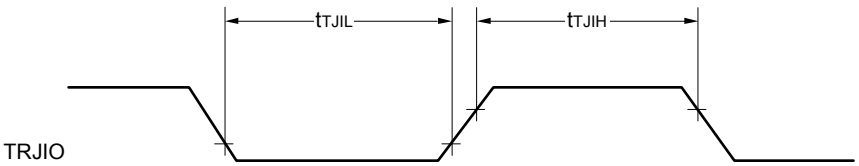
Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 2), mn = 00, 01, 02, 10, 12, 13)

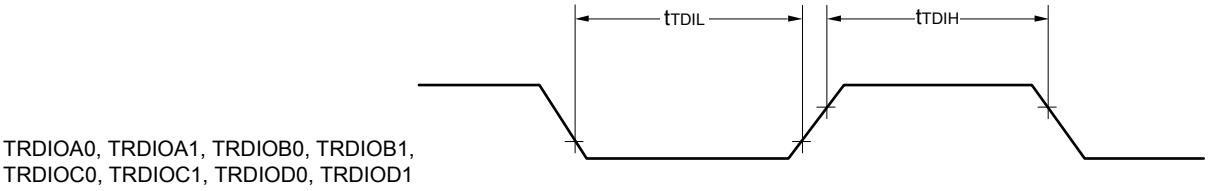
(1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

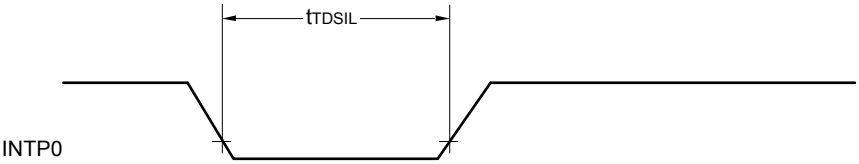
(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = 0 V)(2/2)

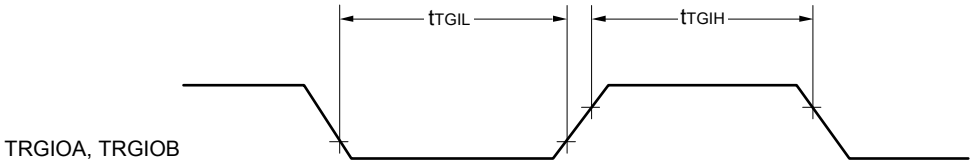
Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.80	4.36	mA
					V_{DD} = 3.0 V		0.80	4.36	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.49	3.67	
					V_{DD} = 3.0 V		0.49	3.67	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.62	3.42	
					V_{DD} = 3.0 V		0.62	3.42	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.4	2.85	
					V_{DD} = 3.0 V		0.4	2.85	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		0.37	2.08	
					V_{DD} = 3.0 V		0.37	2.08	
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.28	2.45	mA
					Resonator connection		0.40	2.57	
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.28	2.45	
					Resonator connection		0.40	2.57	
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.19	1.28	
					Resonator connection		0.25	1.36	
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.19	1.28	
					Resonator connection		0.25	1.36	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5, T_A = -40°C	Square wave input		0.25	0.57	µA
					Resonator connection		0.44	0.76	
				f_{SUB} = 32.768 kHz Note 5, T_A = +25°C	Square wave input		0.30	0.57	
					Resonator connection		0.49	0.76	
				f_{SUB} = 32.768 kHz Note 5, T_A = +50°C	Square wave input		0.36	1.17	
					Resonator connection		0.59	1.36	
				f_{SUB} = 32.768 kHz Note 5, T_A = +70°C	Square wave input		0.49	1.97	
					Resonator connection		0.72	2.16	
				f_{SUB} = 32.768 kHz Note 5, T_A = +85°C	Square wave input		0.97	3.37	
					Resonator connection		1.16	3.56	
				f_{SUB} = 32.768 kHz Note 5, T_A = +105°C	Square wave input		3.20	17.10	
					Resonator connection		3.40	17.50	
	I_{DD3} Note 6	STOP mode Note 8	T_A = -40°C				0.18	0.51	µA
			T_A = +25°C				0.24	0.51	
			T_A = +50°C				0.29	1.10	
			T_A = +70°C				0.41	1.90	
			T_A = +85°C				0.90	3.30	
			T_A = +105°C				3.10	17.00	

(**Notes** and **Remarks** are listed on the next page.)


tTJIL
tTJIH
TRJIO


tTDIL
tTDIH
TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1,
TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1


tTDSIL
INTP0


tTGIL
tTGIH
TRGIOA, TRGIOB

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

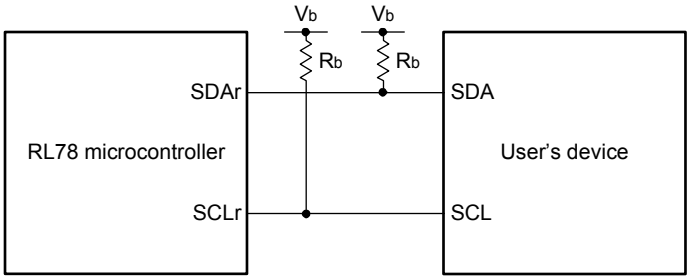
(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ 4/f_{CLK}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	600		ns
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	1000		ns
			2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ	2300		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 150		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 340		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 916		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 24		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 36		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 100		ns

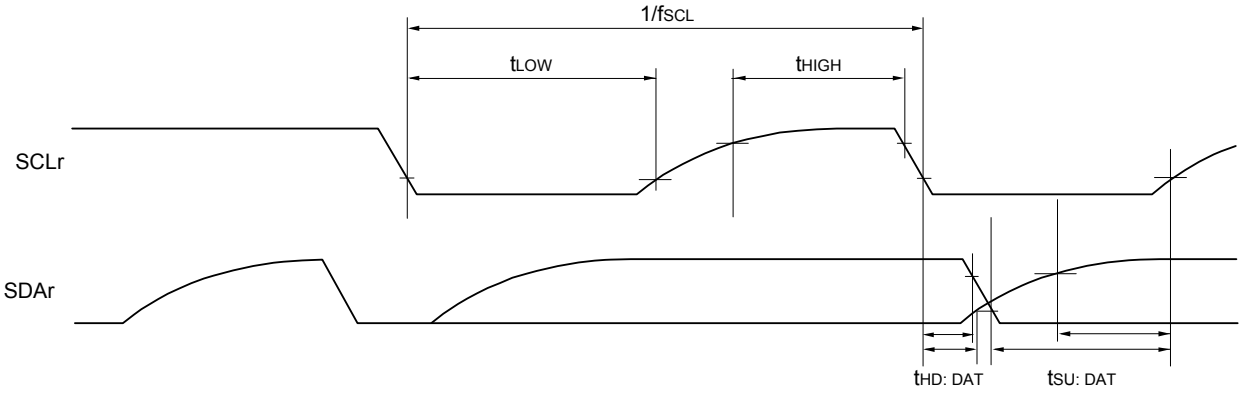
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed two pages after the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remark 1. R_b[Ω]: Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

Remark 2. r: IIC number (r = 00, 01, 10, 11, 20, 30, 31), g: PIM, POM number (g = 0, 1, 3 to 5, 14)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 2), mn = 00, 01, 02, 10, 12, 13)

3.6.4 Comparator

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref			0		EV_{DD0} - 1.4	V
	Ivcmp			-0.3		EV_{DD0} + 0.3	V
Output delay	td	V_{DD} = 3.0 V Input slew rate > 50 mV/µs	Comparator high-speed mode, standard mode			1.2	µs
			Comparator high-speed mode, window mode			2.0	µs
			Comparator low-speed mode, standard mode		3.0	5.0	µs
High-electric-potential reference voltage	VTW+	Comparator high-speed mode, window mode			0.76 V_{DD}		V
Low-electric-potential reference voltage	VTW-	Comparator high-speed mode, window mode			0.24 V_{DD}		V
Operation stabilization wait time	t_{CMP}			100			µs
Internal reference voltage Note	V_{BGR}	2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode		1.38	1.45	1.50	V

Note Not usable in sub-clock operation or STOP mode.

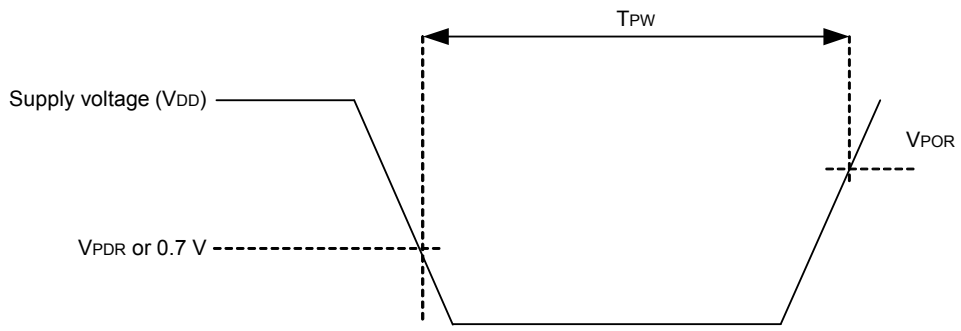
3.6.5 POR circuit characteristics

(T_A = -40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	V_{POR}	Voltage threshold on V_{DD} rising	1.45	1.51	1.57	V
	V_{PDR}	Voltage threshold on V_{DD} falling Note 1	1.44	1.50	1.56	V
Minimum pulse width Note 2	T_{PW}		300			µs

Note 1. However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 3.4 AC Characteristics.

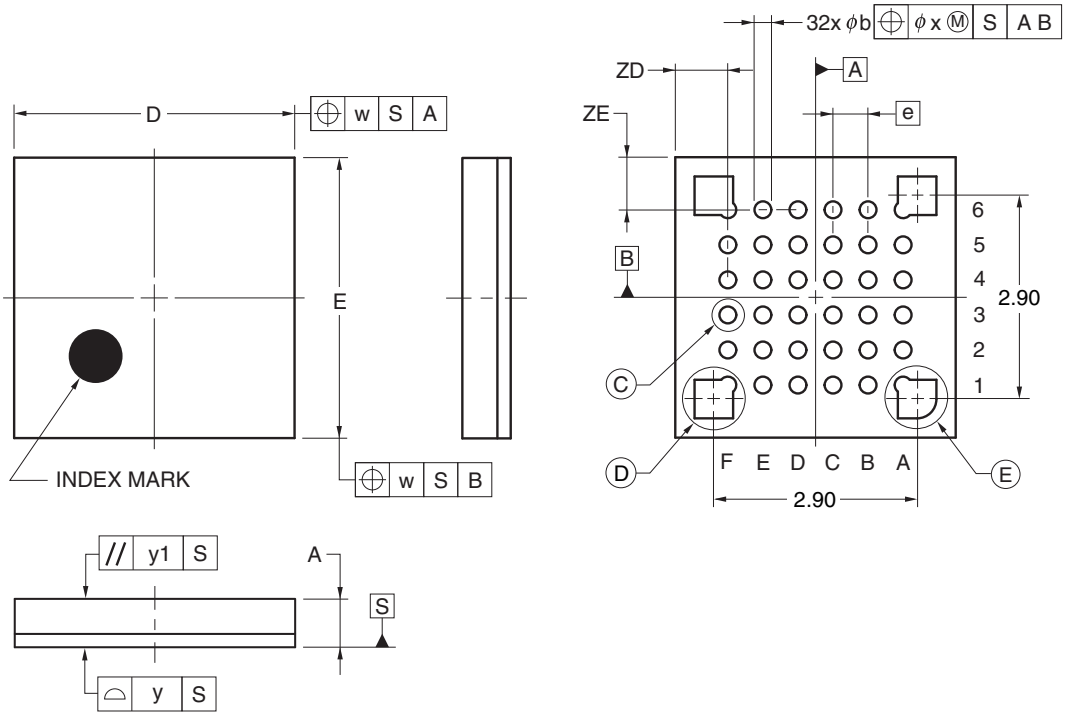
Note 2. Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).

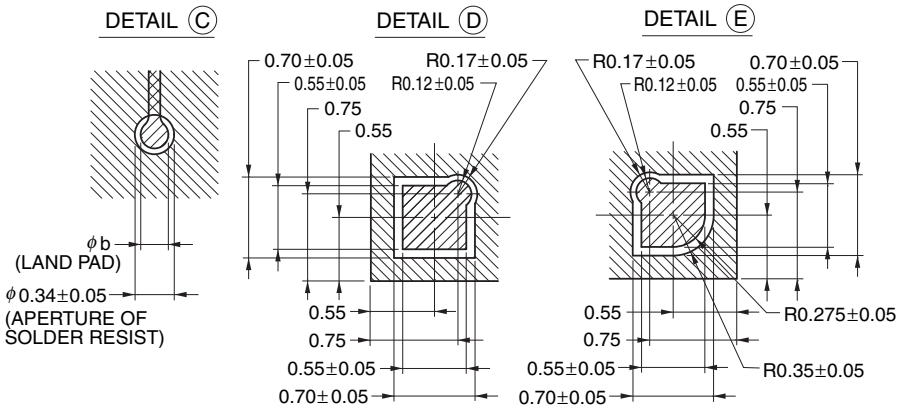


4.3 36-pin products

R5F104CAALA, R5F104CCALA, R5F104CDALA, R5F104CEALA, R5F104CFALA, R5F104CGALA
R5F104CAGLA, R5F104CCGLA, R5F104CDGLA, R5F104CEGLA, R5F104CFGLA, R5F104CGGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023



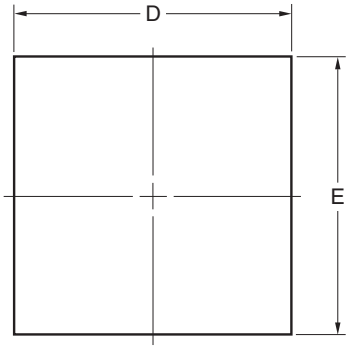


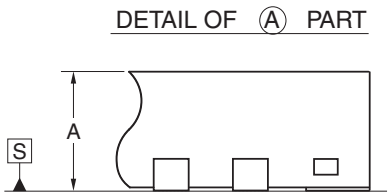
(UNIT:mm)

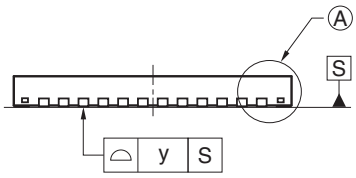
ITEM	DIMENSIONS
D	4.00±0.10
E	4.00±0.10
w	0.20
e	0.50
A	0.69±0.07
b	0.24±0.05
x	0.05
y	0.08
y1	0.20
ZD	0.75
ZE	0.75

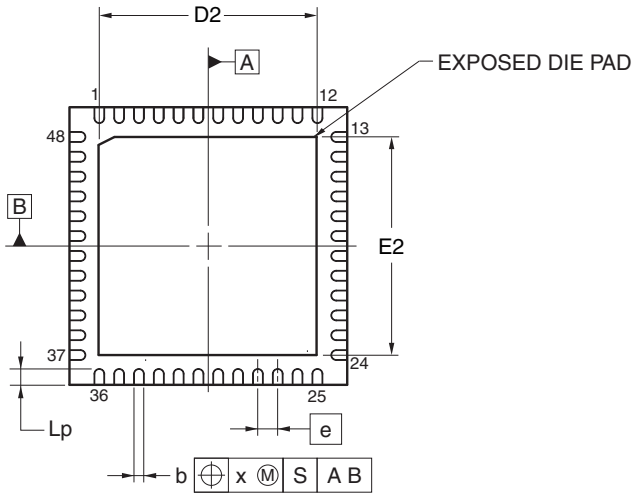
R5F104GAANA, R5F104GCANA, R5F104GDANA, R5F104GEANA, R5F104GFANA, R5F104GGANA, R5F104GHANA, R5F104GJANA
R5F104GADNA, R5F104GCDNA, R5F104GDDNA, R5F104GEDNA, R5F104GFDNA, R5F104GGDNA, R5F104GHDNA, R5F104GJDNA
R5F104GAGNA, R5F104GCGNA, R5F104GDGNA, R5F104GEGNA, R5F104GFGNA, R5F104GGGNA, R5F104GHGNA, R5F104GJGNA
R5F104GKANA, R5F104GLANA
R5F104GKGNA, R5F104GLGNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PJN-A P48K8-50-5B4-5	0.13









Referance Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.95	7.00	7.05
E	6.95	7.00	7.05
A	0.70	0.75	0.80
b	0.18	0.25	0.30
e	—	0.50	—
Lp	0.30	0.40	0.50
x	—	—	0.05
y	—	—	0.05

ITEM		D2			E2		
		MIN	NOM	MAX	MIN	NOM	MAX
EXPOSED DIE PAD VARIATIONS	A	5.45	5.50	5.55	5.45	5.50	5.55

REVISION HISTORY	RL78/G14 Datasheet

Rev.	Date	Description	
		Page	Summary
3.20	Jan 05, 2015	p.135, 137, 139, 141, 143, 145	Modification of specifications in 3.3.2 Supply current characteristics
		p.197	Modification of part number in 4.7 52-pin products
3.30	Aug 12, 2016	p.143, 145	Addition of maximum values in (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products of 3.3.2 Supply current characteristics

NOTES FOR CMOS DEVICES

(1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).

(2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

(3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

(4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

(5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

(6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.